

80V N-Ch Power MOSFET

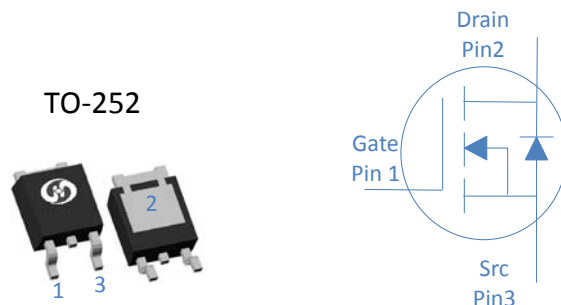
Feature

- ◇ High Speed Power Switching, Logic Level
- ◇ Enhanced Body diode dv/dt capability
- ◇ Enhanced Avalanche Ruggedness
- ◇ 100% UIS Tested, 100% Rg Tested
- ◇ Lead Free

V_{DS}		80	V
$R_{DS(on),typ}$	$V_{GS}=10V$	4.3	mΩ
$R_{DS(on),typ}$	$V_{GS}=4.5V$	5.9	mΩ
I_D (Silicon Limited)		110	A
I_D (Package Limited)		70	A

Application

- ◇ Synchronous Rectification in SMPS
- ◇ Hard Switching and High Speed Circuit
- ◇ Power Tools
- ◇ UPS
- ◇ Motor Control



Part Number	Package	Marking
HGD058N08SL	TO-252	GD058N08SL

Absolute Maximum Ratings at $T_j=25^\circ\text{C}$ (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	$T_C=25^\circ\text{C}$	110	A
		$T_C=100^\circ\text{C}$	78	
		$T_C=25^\circ\text{C}$	70	
Continuous Drain Current (Package Limited)		$T_C=25^\circ\text{C}$	70	
Drain to Source Voltage	V_{DS}	-	80	V
Gate to Source Voltage	V_{GS}	-	± 20	V
Pulsed Drain Current	I_{DM}	-	380	A
Avalanche Energy, Single Pulse	E_{AS}	$L=0.3\text{mH}, T_C=25^\circ\text{C}$	240	mJ
Power Dissipation	P_D	$T_C=25^\circ\text{C}$	150	W
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to 175	$^\circ\text{C}$

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Case	$R_{\theta JC}$	1	$^\circ\text{C/W}$
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	46	$^\circ\text{C/W}$

Electrical Characteristics at T_J=25°C (unless otherwise specified)
Static Characteristics

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	80	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1	1.7	2.4	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0V, V_{DS}=80V, T_J=25^\circ C$	-	-	1	μA
		$V_{GS}=0V, V_{DS}=80V, T_J=100^\circ C$	-	-	100	
Gate to Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	4.3	5.8	$m\Omega$
		$V_{GS}=4.5V, I_D=20A$	-	5.9	8.0	$m\Omega$
Transconductance	g_{fs}	$V_{DS}=5V, I_D=20A$	-	65	-	S
Gate Resistance	R_G	$V_{GS}=0V, V_{DS}$ Open, $f=1MHz$	-	1.5	-	Ω

Dynamic Characteristics

Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=40V, f=1MHz$	-	3130	-	pF
Output Capacitance	C_{oss}		-	385	-	
Reverse Transfer Capacitance	C_{rss}		-	18	-	
Total Gate Charge (10V)	$Q_g(10V)$	$V_{DD}=40V, I_D=20A, V_{GS}=10V$	-	46	-	nC
Total Gate Charge (4.5V)	$Q_g(4.5V)$		-	22	-	
Gate to Source Charge	Q_{gs}		-	9	-	
Gate to Drain (Miller) Charge	Q_{gd}		-	8	-	
Turn on Delay Time	$t_{d(on)}$	$V_{DD}=40V, I_D=20A, V_{GS}=10V, R_G=10\Omega,$	-	11	-	ns
Rise time	t_r		-	7	-	
Turn off Delay Time	$t_{d(off)}$		-	38	-	
Fall Time	t_f		-	9	-	

Reverse Diode Characteristics

Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_F=20A$	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R=40V, I_F=20A, di_F/dt=400A/\mu s$	-	48	-	ns
Reverse Recovery Charge	Q_{rr}		-	190	-	nC

Fig 1. Typical Output Characteristics

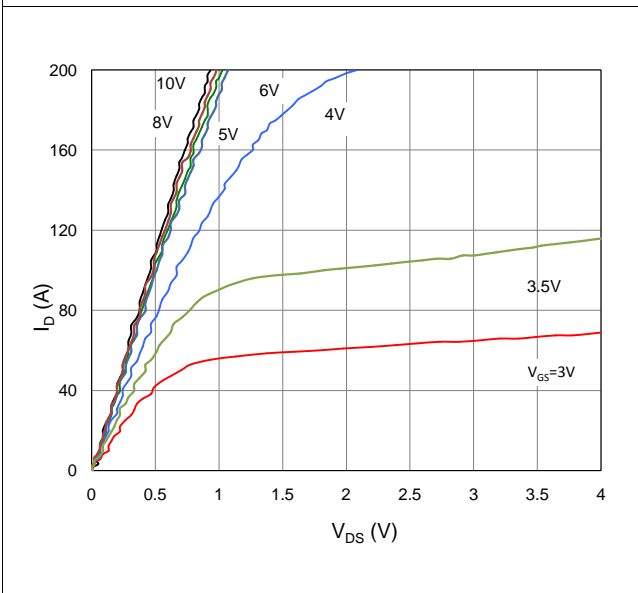


Figure 2. On-Resistance vs. Gate-Source Voltage

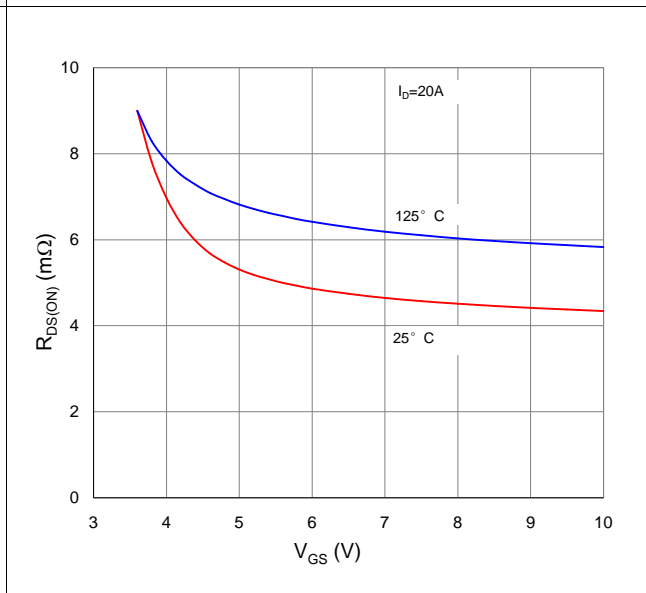


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

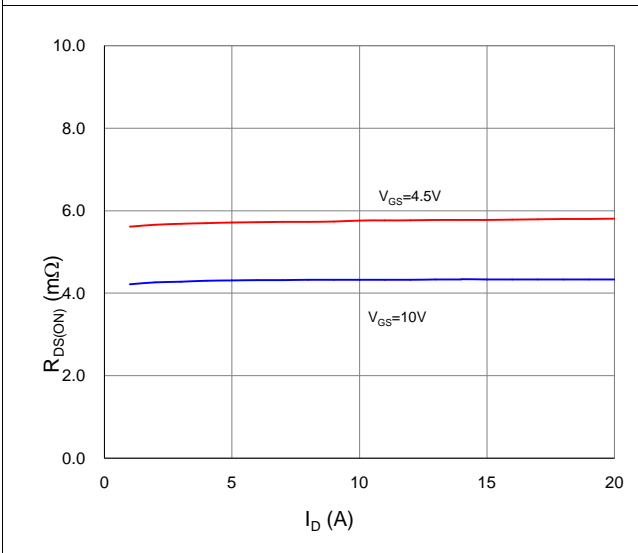


Figure 4. Normalized On-Resistance vs. Junction Temperature

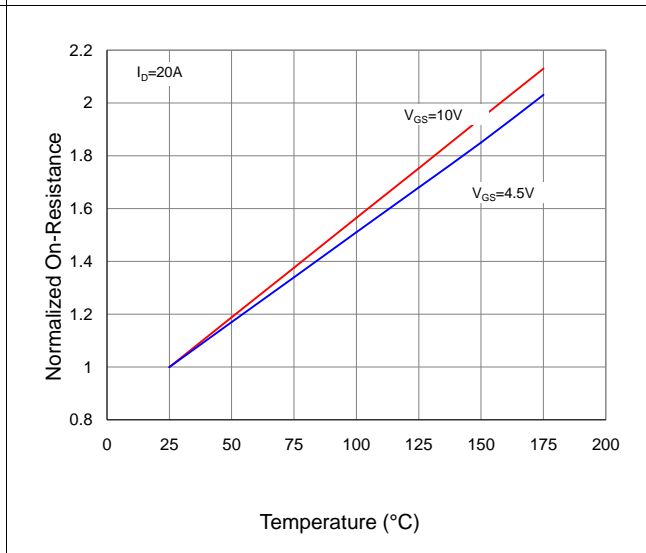


Figure 5. Typical Transfer Characteristics

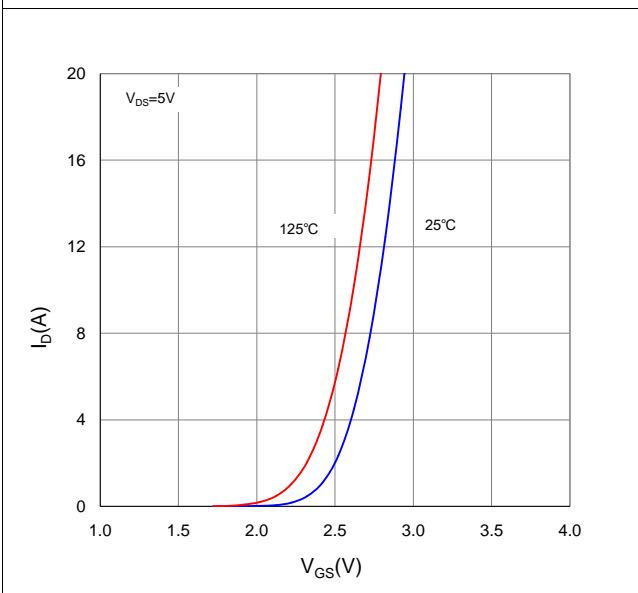


Figure 6. Typical Source-Drain Diode Forward Voltage

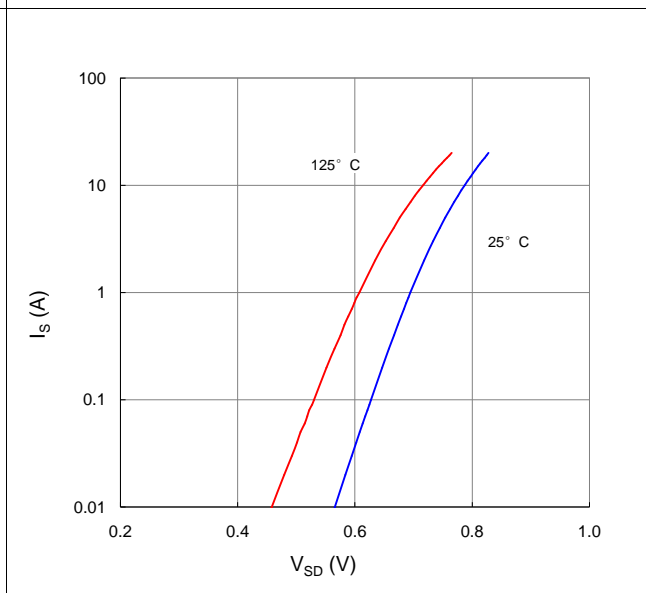


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

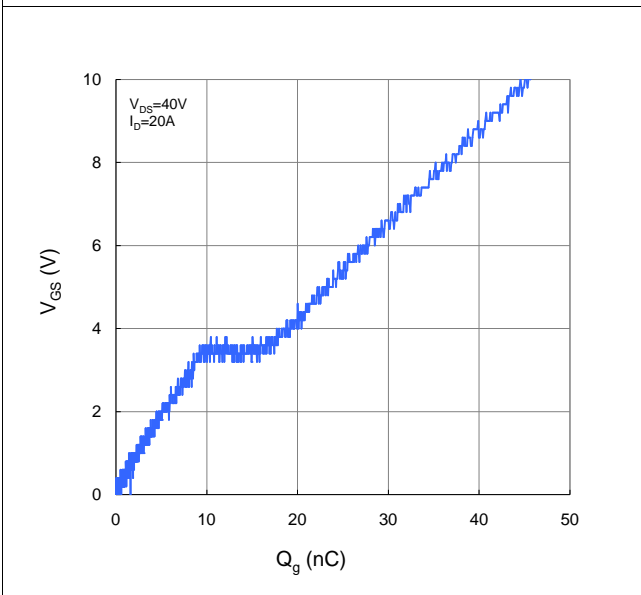


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

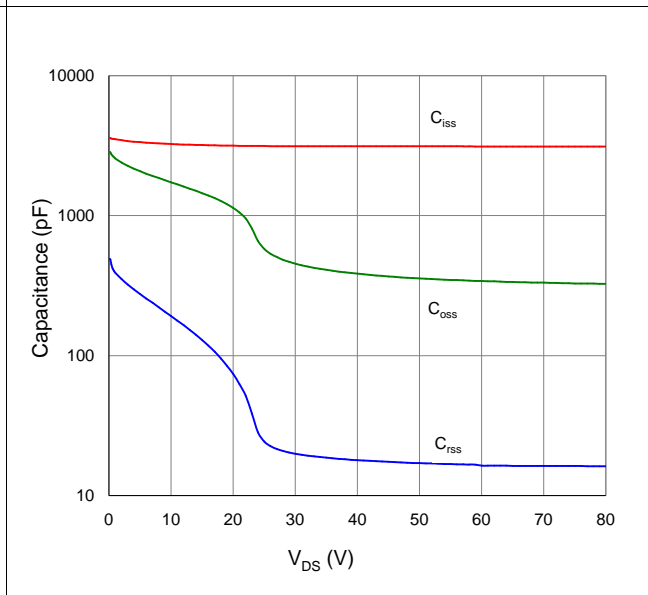


Figure 9. Maximum Safe Operating Area

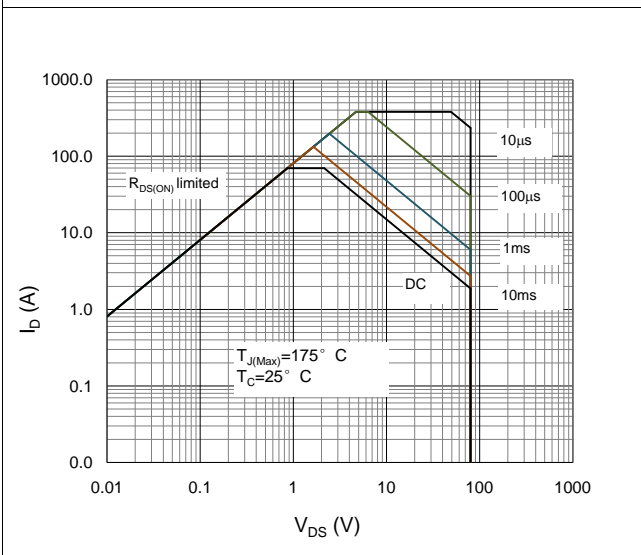


Figure 10. Maximum Drain Current vs. Case Temperature

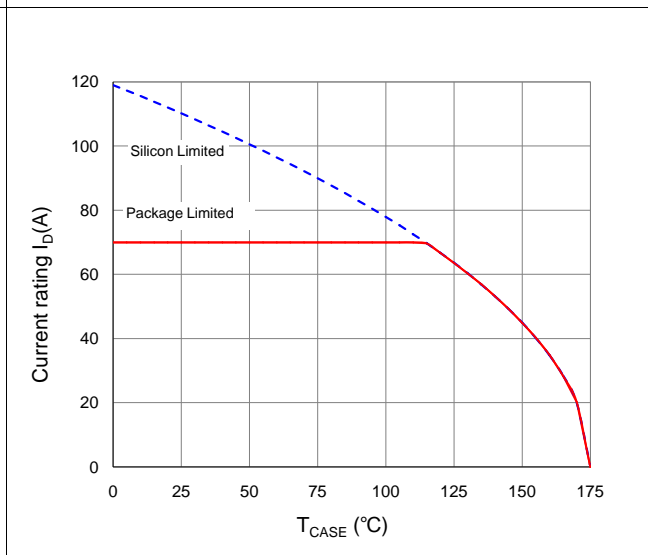
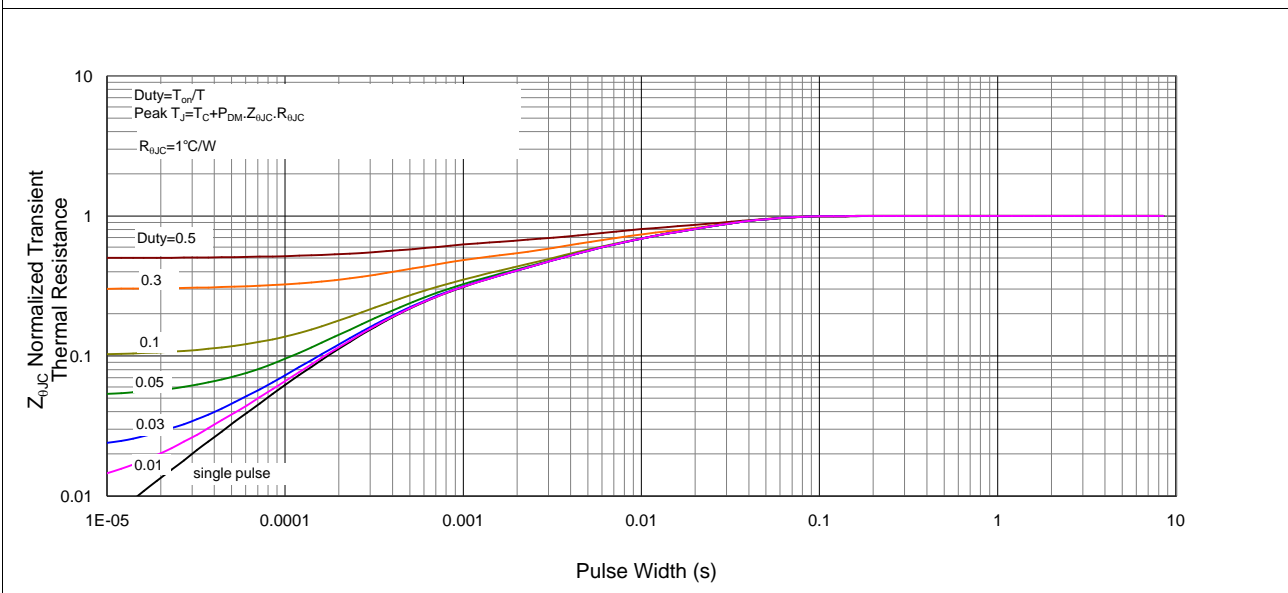
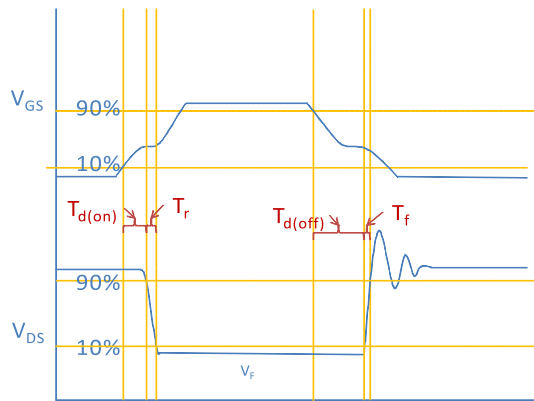
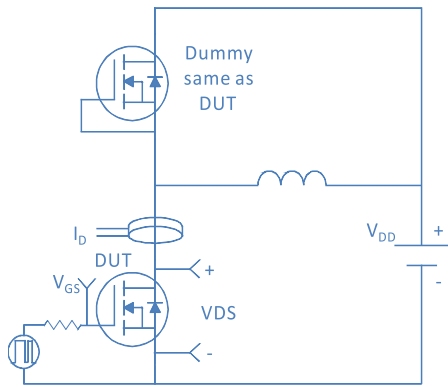


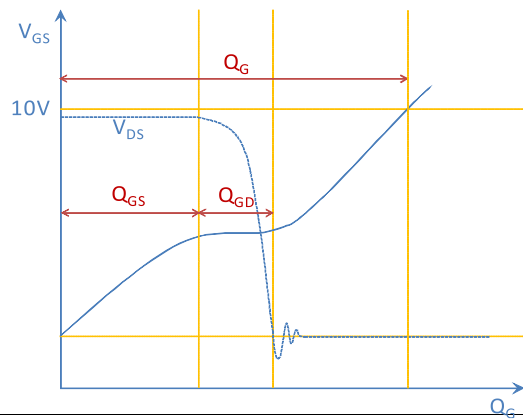
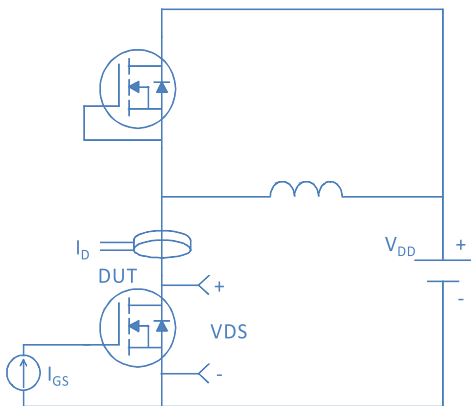
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Case



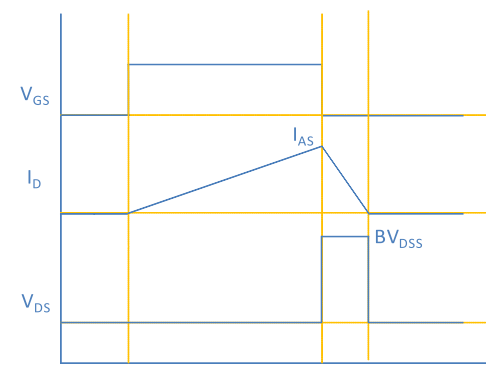
Inductive switching Test



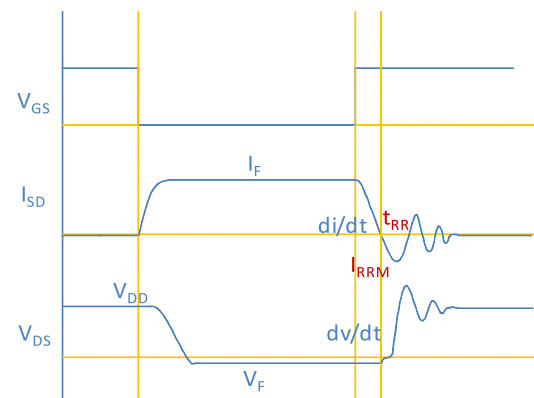
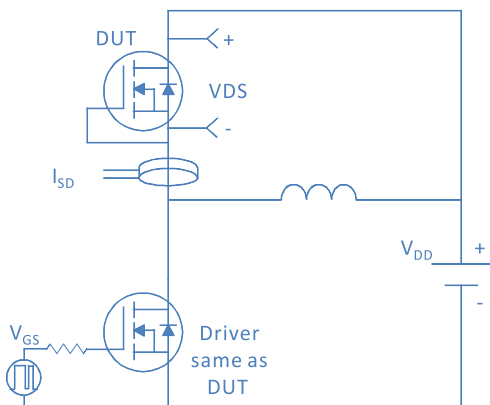
Gate Charge Test



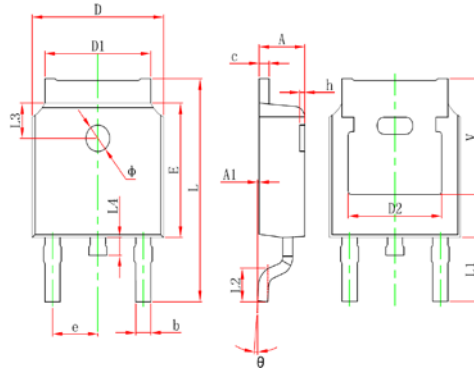
Uclamped Inductive Switching (UIS) Test



Diode Recovery Test



TO-252, 2 leads



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	